

MOSFETs Silicon N-Channel MOS (DTMOSIV)

TK20V60W

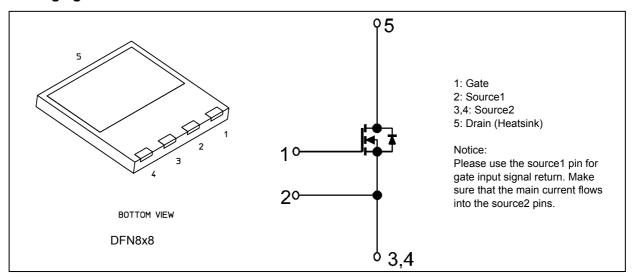
1. Applications

· Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)}$ = 0.136 Ω (typ.) by used to Super Junction Structure : DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode: $V_{th} = 2.7$ to 3.7 V ($V_{DS} = 10$ V, $I_D = 1$ mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

| Characteristics | Symbol | Rating | Unit | |
|--|----------|------------------|------------|----|
| Drain-source voltage | | V_{DSS} | 600 | V |
| Gate-source voltage | | V _{GSS} | ±30 | |
| Drain current (DC) | (Note 1) | I _D | 20 | Α |
| Drain current (pulsed) | (Note 1) | I _{DP} | 80 | |
| Power dissipation (T _c = 25 | 5°C) | P_{D} | 156 | W |
| Single-pulse avalanche energy | (Note 2) | E _{AS} | 200 | mJ |
| Avalanche current | | I _{AR} | 5 | Α |
| Reverse drain current (DC) | (Note 1) | I _{DR} | 20 | |
| Reverse drain current (pulsed) | (Note 1) | I _{DRP} | 80 | |
| Channel temperature | | T _{ch} | 150 | °C |
| Storage temperature | | T _{stg} | -55 to 150 | |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



5. Thermal Characteristics

| Characteristics | Symbol | Max | Unit |
|------------------------------------|-----------------------|-----|------|
| Channel-to-case thermal resistance | R _{th(ch-c)} | 0.8 | °C/W |

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 14 mH, R_G = 25 Ω , I_{AR} = 5 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



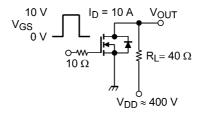
6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25°C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|----------------------|---|-----|-------|------|------|
| Gate leakage current | I _{GSS} | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$ | _ | _ | ±1 | μА |
| Drain cut-off current | I _{DSS} | V _{DS} = 600 V, V _{GS} = 0 V | _ | _ | 10 | |
| Drain-source breakdown voltage | V _{(BR)DSS} | I _D = 10 mA, V _{GS} = 0 V | 600 | _ | _ | V |
| Gate threshold voltage | V_{th} | V _{DS} = 10 V, I _D = 1 mA | 2.7 | _ | 3.7 | |
| Drain-source on-resistance | R _{DS(ON)} | V _{GS} = 10 V, I _D = 10 A | | 0.136 | 0.17 | Ω |

6.2. Dynamic Characteristics (T_a = 25°C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|--------------------|---|-----|------|-----|------|
| Input capacitance | C _{iss} | V _{DS} = 300 V, V _{GS} = 0 V, f = 1 MHz | _ | 1680 | _ | pF |
| Reverse transfer capacitance | C _{rss} | | _ | 7 | _ | |
| Output capacitance | C _{oss} | | _ | 40 | _ | |
| Effective output capacitance | C _{o(er)} | V _{DS} = 0 to 400 V, V _{GS} = 0 V | _ | 70 | _ | |
| Gate resistance | r _g | V _{DS} = OPEN, f = 1 MHz | _ | 1.5 | _ | Ω |
| Switching time (rise time) | t _r | See Figure 6.2.1 | _ | 25 | _ | ns |
| Switching time (turn-on time) | t _{on} | | _ | 50 | _ | |
| Switching time (fall time) | t _f | | _ | 6 | _ | |
| Switching time (turn-off time) | t _{off} | | _ | 100 | _ | |
| MOSFET dv/dt ruggedness | dv/dt | V _{DD} = 0 to 400 V, I _D = 5 A | 50 | | | V/ns |



 $Duty \leq 1 \ \%, \ t_W = 10 \ \mu s$

Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25°C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|------------------|---|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg | $V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$ | _ | 48 | | nC |
| Gate-source charge 1 | Q _{gs1} | | | 11 | | |
| Gate-drain charge | Q_{gd} | | | 22 | | |

6.4. Source-Drain Characteristics (T_a = 25°C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|-------------------------------|-----------------|--|-----|------|------|------|
| Diode forward voltage | V_{DSF} | I _{DR} = 20 A, V _{GS} = 0 V | - | 1 | -1.7 | V |
| Reverse recovery time | t _{rr} | I _{DR} = 10 A, V _{GS} = 0 V | | 330 | | ns |
| Reverse recovery charge | Q_{rr} | -dI _{DR} /dt = 50 A/μs | _ | 2.9 | | μС |
| Peak reverse recovery current | I _{rr} | | _ | 16 | _ | Α |
| Diode dv/dt ruggedness | dv/dt | I _{DR} = 10 A, V _{GS} = 0 V, V _{DD} = 400 V | 15 | _ | | V/ns |



7. Marking

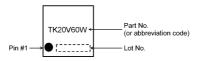
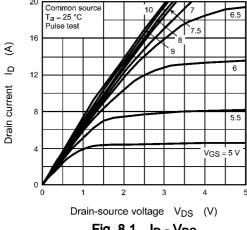
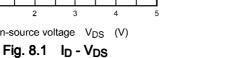


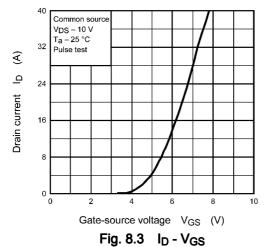
Fig. 7.1 Marking

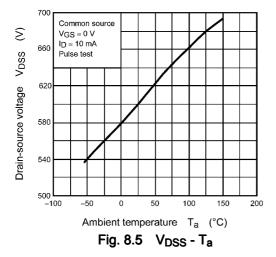
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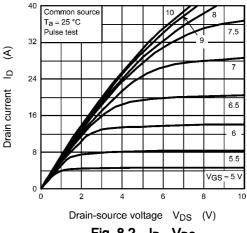
8. Characteristics Curves (Note)

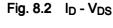


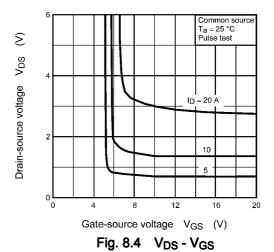












Common source VGS = 10 V T_a = 25 °C Drain-source on-resistance RDS(ON) (Ω) Pulse test 0.01 1000 Drain current I_D (A)

Fig. 8.6 R_{DS(ON)} - I_D

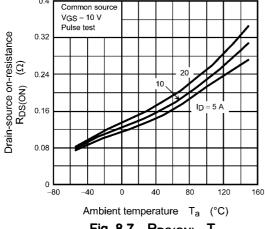


Fig. 8.7 R_{DS(ON)} - T_a

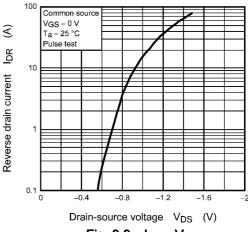


Fig. 8.8 I_{DR} - V_{DS}

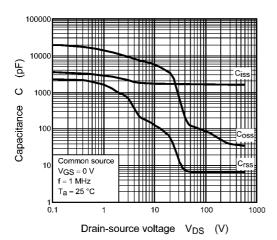


Fig. 8.9 C - V_{DS}

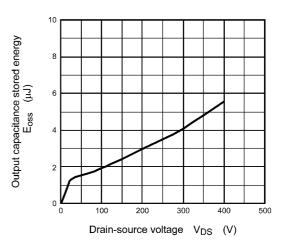


Fig. 8.10 E_{OSS} - V_{DS}

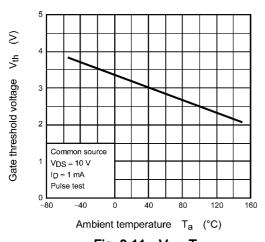


Fig. 8.11 V_{th} - T_a

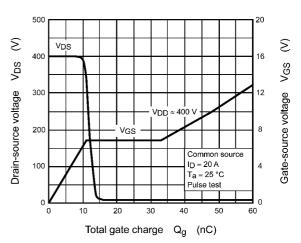


Fig. 8.12 Dynamic Input/Output Characteristics

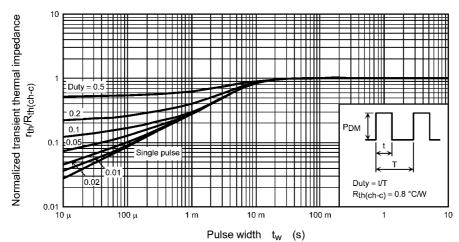


Fig. 8.13 r_{th} - t_w (Guaranteed Maximum)

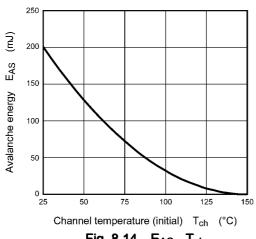


Fig. 8.14 E_{AS} - T_{ch} (Guaranteed Maximum)

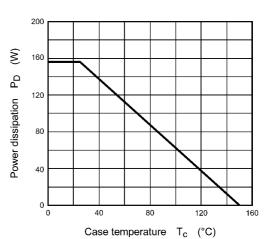


Fig. 8.15 P_D - T_c (Guaranteed Maximum)

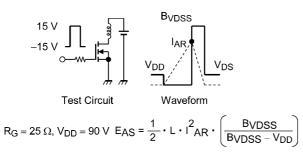


Fig. 8.16 Test Circuit/Waveform

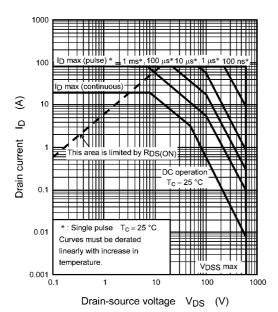


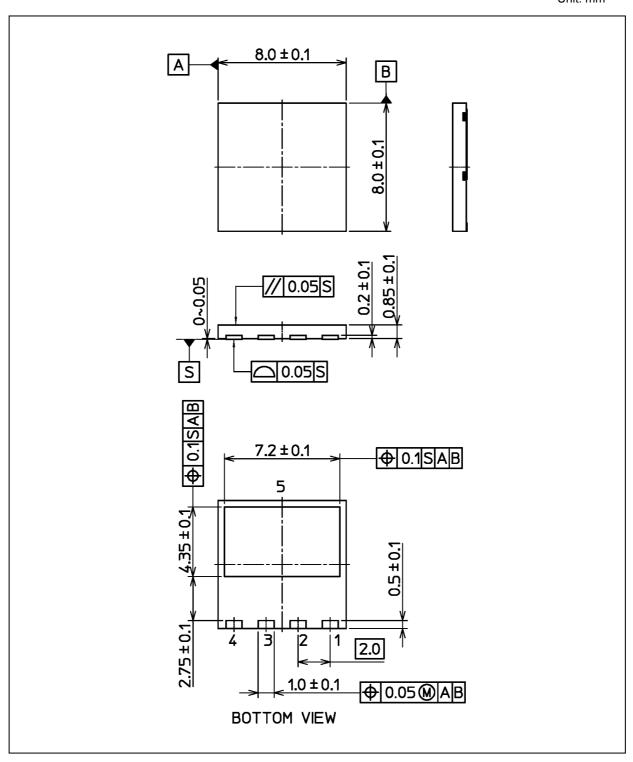
Fig. 8.17 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.175 g (typ.)

| | Package Name(s) |
|------------------|-----------------|
| TOSHIBA: 2-8T1A | |
| Nickname: DFN8x8 | |



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